Amendments to the Specification:

Please replace the paragraph that begins at page 7, line 12 with the following amended paragraph:

> The substrate 100 has a p-doping of about 3×10^{15} 1/cm^3. On a surface 102 of the substrate 100 a gate structure 104 is formed including a gate polysilicon 106 and a gate oxide 108 arranged between the gate polysilicon 106 and the substrate 100. Within the substrate 100 further an n^+-source area 110 and an n^+-drain area 112 is formed. The regions 112a, 112b, 112c indicate drain area regions with different doping concentrations. Below the gate oxide 108 a laterally diffused channel area 114 is formed comprising a p-doping in the area of about 2×10^{17} 1/cm^3. The source area 110 and the drain area respectively comprise n-dopings of about 2×10^{20} 1/cm^3.

Please replace the paragraph that begins at page 9, line 27 with the following amended paragraph:

> ~~Fig. 2~~ Curve 2 shows the course of the input characteristic line after the additional p-region 118 was implanted into the LDD area 116. As it may be seen, hereby the characteristic line is lowered, as due to the p-region 118 the resistance in the LDD area 116 is increased and so the drain current compared to the LDD area correspondingly decreases without an additional p-region 118 (curve 1).